

Capacitor Process Module

4. Capacitor dielectric formation
5. Upper electrode formation
6. Upper electrode doping
7. Upper electrode anneal
8. Photo mask to define upper electrode
9. Upper electrode etch
10. Capacitor dielectric removal
- 10a. RTO

Standard Submicron Core Technology Flow continued

11. ARL/PEARL formation
12. Photo mask to define lower electrode
13. Lower electrode etch
14. Poly oxidation for transistor and subsequent steps,

where steps 9-11 are shown in Figures 2-5. Steps 1-3 and steps 11 on are part of the transistor fabrication process, while steps 4-10a are specific to capacitor formation. These steps differ from the more or less generic prior art by the inclusion of step 10a. The next few paragraphs describe the details of these steps according to this preferred embodiment.

In the Figures:

Please add the attached Figure 12.

In the Claims:

Please replace claim 17 with the following (a marked up version is in the Appendix):

17.(Amended) The method according to claim 16, wherein prior to forming said insulating layer by deposition, an anneal is performed.

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